

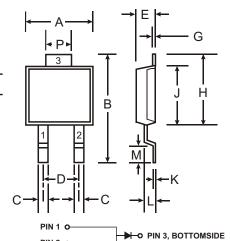
# 7A SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER POWERMITE® 3

# Features NOT RECOMMENDED FOR NEW DESIGNS

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- Low Reverse Current
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

#### **Mechanical Data**

- Case: POWERMITE®3
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See DiagramMarking: Type Number
- Weight: 0.072 grams (approximate)



Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

POWERMITE®3			
Dim	Min	Max	
Α	4.03	4.09	
В	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
М	.36	.46	
Р	1.73	1.83	
All Dimensions in mm			

#### **Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	42	V
Average Rectified Output Current (See also figure 4)	lo	7	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load @ $T_C = 55$ °C	I <sub>FSM</sub>	100	А
Typical Thermal Resistance Junction to Soldering Point	$R_{ heta JS}$	2.5	°C/W
Operating Temperature Range	Tj	-65 to +125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C

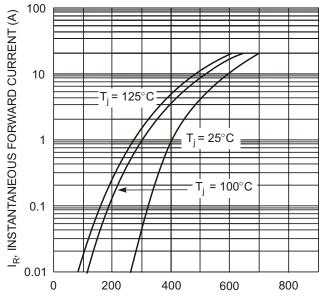
#### **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	60	_	_	V	I <sub>R</sub> = 0.5mA
Forward Voltage	V <sub>F</sub>		0.49 0.38 0.57 0.46	0.52 — 0.60 —	V	$\begin{array}{l} I_F = 3.5A, \ T_j = 25^{\circ}C \\ I_F = 3.5A, \ T_j = 125^{\circ}C \\ I_F = 7A, \ T_j = 25^{\circ}C \\ I_F = 7A, \ T_j = 125^{\circ}C \end{array}$
Reverse Current (Note 1)	I <sub>R</sub>		5 10	200 20	μA mA	$T_j = 25$ °C, $V_R = 60$ V $T_j = 125$ °C, $V_R = 60$ V
Total Capacitance	Ст	_	375		pF	f = 1.0MHz, V <sub>R</sub> = 4.0V DC

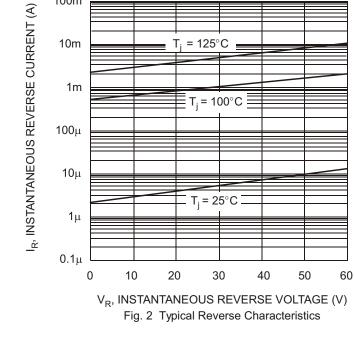
Notes: 1. Short duration test pulse used to minimize self-heating effect.

### NOT RECOMMENDED FOR NEW DESIGNS

100m



V<sub>F</sub>, INSTANTANEOUS FORWARD VOLTAGE (mV) Fig. 1 Typical Forward Characteristics



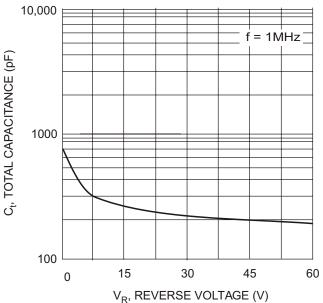
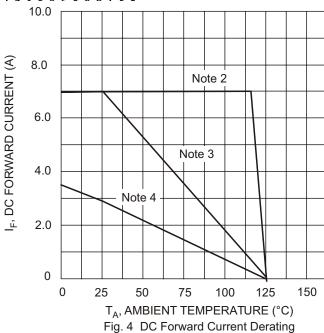
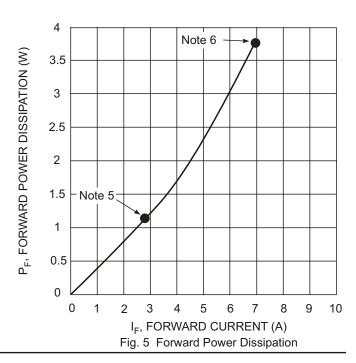


Fig. 3 Typical Total Capacitance vs. Reverse Voltage







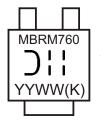
#### Ordering Information (Note 7)

Device	Packaging	Shipping
MBRM760-13	POWERMITE®3	5000/Tape & Reel

Notes

- 2. TA = TSOLDERING POINT,  $R_{\theta JS} = 2.5^{\circ}C/W$ ,  $R_{\theta SA} = 0^{\circ}C/W$ .
- 3. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\theta JA}$  in range of 25-30°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R<sub>0JA</sub> in range of 85-90°C/W.
- 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 4.
- 6. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.
- 7. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



MBRM760 = Product type marking code

Oli = Manufacturers' code marking

YYWW = Date code marking

YY = Last digit of year ex: 02 for 2002

WW = Week code 01 to 52

(K) = Factory Designator

NOT RECOMMENDED FOR NEW DESIGNS